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Attorney Docket No. P119-US

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of: Doan et al.

Art Unit: 1765

Serial No.: 10/805,610

Examiner: Not Yet Assigned

Filed: 3/18/04

For: **A MICROELECTROMECHANICAL STRUCTURE AND A
METHOD FOR MAKING THE SAME**

INFORMATION DISCLOSURE STATEMENT
PURSUANT TO 37 CFR 1.97(b)

Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-145

Sir:

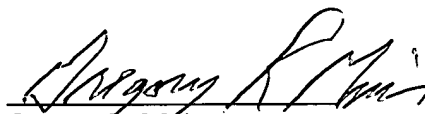
The attention of the Patent and Trademark Office is hereby directed to the documents listed on the attached PTO Form 1449. Copies of the cited references are enclosed.

No fee or certification is required in connection with this Information Disclosure Statement, since it is being submitted prior to the last of (1) issuance of a first official action on the merits and (2) expiration of the three month period following filing of the above-captioned application.

The above information is presented so that the Patent and Trademark Office can determine any materiality thereof to the claimed invention. It is respectfully requested that the information be considered during the prosecution of this application and that the cited documents be listed on the front page of any patent issuing from this application.

The Patent Office is authorized to charge our Deposit Account No. 501516 for any fee which it deems to be required to effect consideration of this statement.

Respectfully submitted,

A handwritten signature in black ink, appearing to read "Gregory R. Muir", is written over a horizontal line.

Gregory R. Muir
Attorney for Applicant(s)
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PTO/SB/08A (10-01)

Approved for use through 10/31/2002. OMB 0651-0031

U.S. Patent and Trademark Office: U.S. DEPARTMENT OF COMMERCE

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Substitute for form 1449A/PTO INFORMATION DISCLOSURE STATEMENT BY APPLICANT (use as many sheets as necessary)			Complete if Known		
			Application Number	10/805,610	
			Filing Date	3/18/04	
			First Named Inventor	Doan	
			Art Unit	1765	
			Examiner Name	Not Yet Assigned	
Sheet	1	of	6	Attorney Docket Number	P119-US

U.S. PATENT DOCUMENTS					
Examiner Initials ¹	Cite No. ¹	Document Number	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number - Kind Code ² (if known)			
		US- 3,511,727	05-12-1970	Hays, R.G.	
		US- 4,190,488	02-26-1980	Winters, H.F.	
		US- 4,310,380	12-12-1982	Flamm et al.	
		US- 4,498,953	02-12-1985	Cook et al.	
		US- 6,051,503	04-18-2000	Bhardwai, J.K.	
		US- 6,436,229	08-20-2002	Tai et al.	
		US- 6,162,367	12-19-2000	Tai et al.	
		US- 6,290,864 B1	09-18-2001	Patel et al.	
		US- 6,355,181 B1	03-12-2002	McQuarrie, A.D.	
		US- 2001/0002663 A1	06-07-2001	Tai et al.	
		US- 5,439,553	08-08-1995	Grant et al.	
		US- 2002/0033229 A1	03-21-2002	Leboulitz et al.	
		US- 2002/0196524 A1	12-26-2002	Huibers, et al.	
		US- 2003/0054588 A1	03-20-2003	Patel, et al.	
		US- 5,726,480	03-10-1998	Pister, K.S.	
		US- 2002/0185699	12-12-2002	Reid	
		US- 2002/0121502 A1	09-15-2002	Patel, et al.	
		US- 5,835,256	11-10-1998	Huibers, A.	
		US- 2002/0047172 A1	04-25-2002	Reid	
		US- 2003/0166342 A1	09/04/03	Chinn, et al.	

FOREIGN PATENT DOCUMENTS						
Examiner Initials ¹	Cite No. ¹	Foreign Patent Document	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T ⁶
		Country Code ³ - Number ⁴ - Kind Code ⁵ (if known)				
		EP-0704884-A2 ✓	04-03-1996	Mehta, J.		
		EP-0822582-A2 ✓	02-04-1998	Bhardwai, J.K.		
		EP-0822584-A2 ✓	04-04-1998	Bhardwai, J.K.		
		WO-99/49506 ✓	09-30-1999	McQuarrie, A.D.		
		EP-0878824-A2 ✓	11-18-1998	McQuarrie et al.		
		EP-0878824-A3 ✓	01-19-2000	McQuarrie et al.		
		JP-1982/57098679-A ✓	06-18-1982	Tsunetoshi, A.		
		JP-1983/58130529-A ✓	08-04-1983	Yoshihiro et al.		
		JP-1985/60057938-A ✓	04-03-1985	Katsumi et al.		
		WO-98/32163 ✓	07-23-1998	Tai et al.		

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		Number - Kind Code ² (if known)			
		US- 6,409,876 B1	06-25-2002	McQuarrie, et al.	
		US- 6,396,619 B1	05-28-2002	Huibers, et al.	
		US- 6,576,489 B2	06/10/03	Leung, et a	
		US- 6,238,581	05-29-2001	Hawkins, et al.	
		US- 6,115,172	09-05-2000	Jeong	
		US- 6,204,080	03-20-2001	Hwang	
		US- 2003/0071015 A1	04/17/03	Chinn, et al.	
		US- 2002/0164879 A1	11/07/02	Leung, et al.	
		US- 2002/0163051 A1	11/07/02	Gopal, et al.	
		US- 2003/0077878 A1	04/24/03	Kumar, et al.	
		US- 6,197,610 B1	03/06/2001	Toda	
		US- 6,500,356 B2	12/31/02	Goto, et al.	
		US- 2003/0124848 A1	0703/03	Chinn, et al.	
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		US- 2004/0035821	2/26/04	Doan, et al.	
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		Country Code ³ - Number ⁴ - Kind Code ⁵ (if known)				
		JP-1997/09251981-A ✓	09-22-1997	Kazuaki et al.		
		JP-1998/10313128-A ✓	11-24-1998	Hanmin et al.		
		JP-1998/10317169-A ✓	12-02-1998	McQuarrie et al.		
		JP-1986/61187238-A ✓	08-20-1986	Nobuo et al.		
		JP-1986/61270830-A ✓	12-01-1986	Toru, T.		
		JP-1987/62071217-A ✓	04-01-1987	Toru et al.		
		JP-1988/63155713-A ✓	06-28-1988	Tadashi, F.		
		JP-1986/61053732-A ✓	03-17-1986	Arata et al.		
		JP-1986/61134019-A ✓	06-21-1986	Shinji et al.		
		JP-1986/61181131-A ✓	08-13-1986	Shinii et al.		

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INFORMATION DISCLOSURE STATEMENT BY APPLICANT (use as many sheets as necessary)				Application Number	10/805.610
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Sheet	3	of	6	Attorney Docket Number	P119-US

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		Country Code ³ - Number ⁴ - Kind Code ⁵ (if known)				
		JP-1989/01208834-A	08-22-1989	Nobuo et al.		
		JP-1989/10217921-A	08-31-1989	Tsuneo et al.		
		JP-1990/02250323-A	10-08-1990	Susumu et al.		
		JP-1991/03012921-A	01-21-1991	Nobuo et al.		
		JP-1992/04096222-A	03-27-1992	Atsuyuki, A.		
		JP-1995/07029823-A	01-31-1995	Hiroshi, T.		

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		Group Art Unit	1765
		Examiner Name	Not Yet Assigned
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Sheet	4	of	6

OTHER PRIOR ART -- NON PATENT LITERATURE DOCUMENTS			
Examiner Initials*	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published	T ²
		ALIEV et al., "Development of Si(100) Surface Roughness at the Initial Stage of Etching in F ₂ and XeF ₂ Gases Ellipsometric Study", Surface Science 442 (1999), pp. 206-214.	
		GLIDEMEISTER, J.M., "Xenon Difluoride Etching System" (Nov. 17, 1997).	
		HABUKA et al., "Dominant Overall Chemical Reaction in a Chlorine Trifluoride-Silicon-Nitrogen System at Atmospheric Pressure", Japan Journal of Applied Physics Vol. 38 (1999), pp. 6466-6469.	
		HECHT et al., "A Novel X-ray Photoelectron Spectroscopy Study of the Al/SiO ₂ Interface", J. Appl. Phys. Vol. 57 (June 15, 1985), pp. 5256-5261.	
		HOULE, F.A., "Dynamics of SiF ₄ Desorption During Etching of Silicon by XeF ₂ ", IBM Almaden Research Center (April 15, 1987), pp. 1866-1872.	
		FLAMM et al., "XeF ₂ and F-Atom Reactions with Si: Their Significance for Plasma Etching", Solid State Technol. 26, 117 (1983).	
		IBBOTSON et al., "Plasmaless Dry Etching of Silicon with Fluorine-containing Compounds", J. Appl. Phys. Vol. 56 No. 10 (Nov. 1984), pp. 2939-2942.	
		IBBOTSON et al., "Comparison of XeF ₂ and F-atom Reactions with Si and SiO ₂ ", Applied Physics Letter, Vol. 44, 1129 (1984).	
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		VUGTS et al., "Si/XeF ₂ Etching: Temperature Dependence", J. Vac. Sci. Technol. A 14(5) (Sep/Oct 1996), pp. 2766-2774.	
		WINTERS, H.F., "Etch Products from the Reaction of XeF ₂ with SiO ₂ , SiO ₃ , Si ₃ N ₄ , SiC, and Si in the Presence of Ion Bombardment", J. Vac. Sci. Technol. B 1(4) (Oct/Dec 1983), pp. 927-931.	

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INFORMATION DISCLOSURE STATEMENT BY APPLICANT (use as many sheets as necessary)			Application Number	10/805,610
			Filing Date	3/18/04
			First Named Inventor	Doan
			Group Art Unit	1765
			Examiner Name	Not Yet Assigned
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Sheet	5	of	6	

OTHER PRIOR ART -- NON PATENT LITERATURE DOCUMENTS			
Examiner Initials*	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published	T ²
		Kurt Williams, Etch Rates for Micromachining Processing-Part II, 2003 IEEE, Pgs 761-778, Journal of Microelectromechanical Systems, Vol. 12, No. 6, December 2003.	
		WINTERS et al., "The Etching of Silicon with XeF2 Vapor", Appl. Phys. Letter, Vol. 34(1) (January 1, 1979), pp. 70-73.	
		XACTIX, Inc., Marketing Brochure (June 27, 1999).	
		"Xenon Difluoride Isotropic Etch System: Seeing is Believing", Surface Technology Systems Ltd. brochure, Newport, UK (date unknown).	
		CHU et al., "Controlled Pulse-Etching with Xenon Difluoride", International Solid State Sensors and Actuators Conference (Transducers '97), Chicago, IL, Vol. 1 (June 16 - 19, 1997), pp. 665-668 (abstract only).	
		BASSOM et al., "Modeling and Optimizing XeF2-enhanced FIB Milling of Silicon", 25th International Symposium for Testing and Failure Analysis, Santa Clara, CA (Nov. 14 -18, 1999), pp. 255-261 (abstract only).	
		KOHLER et al., "Fabrication of Microlenses by Plasmaless Isotropic Etching Combined with Plastic Moulding", Sens. Actuators A, Phys. (Switzerland), Vol. A53, No. 1-3 (May 1996), pp. 361-363 (abstract only).	
		CHAN et al., "Gas Phase Pulse Etching of Silicon for MEMS with Xenon Difluoride", Engineering Solutions for the Next Millenium: 1999 IEEE Canadian Conference on Electrical and Computer Engineering, Edmonton, Alberta, Vol. 3 (May 9 - 12, 1999), pp. 1637-1642 (abstract only).	
		CHANG et al., "Gas-Phase Silicon Micromachining with Silicon Difluoride", Proceedings of the SPIE - The International Society for Optical Engineering, Vol. 2641 (1995), pp. 117-128 (abstract only).	

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OTHER PRIOR ART – NON PATENT LITERATURE DOCUMENTS			
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		SEBEL et al., "Reaction Layer Dynamics in Ion-Assisted Si/XeF ₂ Etching: Temperature Dependence", J. Vac. Sci. Technol. A, Vac. Surf. Films, Vol. 18, No. 6, (Nov. 2000), pp. 2759-2769 (abstract only).	
		SEBEL et al., "Silicon Etch Rate Enhancement by Traces of Metal", J. Vac. Sci. Technol. A, Vac. Surf. Films, Vol. 17, No. 3, (May/June 1999), pp. 755-762 (abstract only).	
		SUGANO et al., "Study on XeF ₂ Pulse Etching Using Wagon Wheel Pattern", Proceedings of the 1999 International Symposium on Micromechanics and Human Science: Towards the New Century, Nagoya, Japan (Nov. 23 - 26, 1999), pp. 163-167 (abstract only).	
		WANG et al., "Gas-Phase Silicon Etching with Bromine Trifluoride", International Solid State Sensors and Actuators Conference (Transducers '97), Chicago, IL, Vol. 2 (June 16 - 19, 1997), pp. 1505-1508 (abstract only).	
		MUTHUKUMARAN et al., "Gas-Phase Xenon Difluoride Etching of Microsystems Fabricated Through the Mitel 1.5- μ m CMOS Process", Can. J. Electr. Comput. Eng. (Canada), Vol. 25, No. 1 (Jan. 2000), pp. 35-41 (abstract only).	
		TODA et al., "Thin Beam Bulk Micromachining Based on RIE and Xenon Difluoride Silicon Etching", International Solid State Sensors and Actuators Conference (Transducers '97), Chicago, IL, Vol. 1 (June 16 - 19, 1997), pp. 671-674.	
		SEBEL et al., "Etching of Si Through a Thick Condensed XeF ₂ Layer", J. Vac. Sci. Technol. A, Vac. Surf. Films, Vol. 18, No. 5 (Sept/Oct 2000), pp. 2090-2097 (abstract only).	

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